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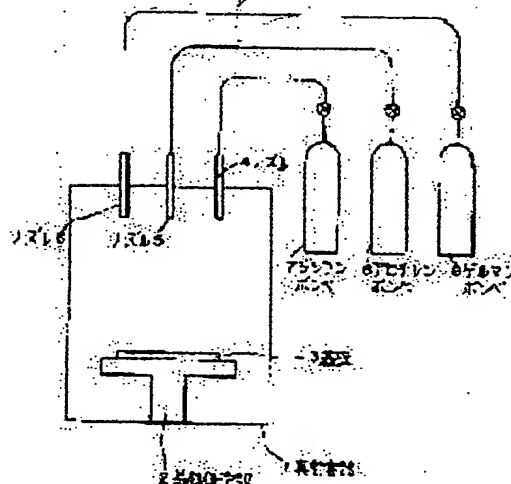
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(54) METHOD AND DEVICE FOR GROWTH OF SILICON FILM

(57)Abstract:

PURPOSE: To uniformly grow a silicon film on a wide area including a recessed part by a method wherein, a silicon film containing carbon and germanium is grown by using gaseous raw material containing silicon atoms, carbon atoms and germanium atoms,

CONSTITUTION: A substrate retaining part 2, having a heating means, is provided in a vacuum container 1. A disilane feeding nozzle 4 and a disilane gas cylinder 7, which is connected to the nozzle 4, are provided above the retaining part. Also, an acetylene-feeding nozzle 5, an acetylene gas cylinder 8 connected to the nozzle 5, a germanium feeding nozzle 6, and a germanium gas cylinder 9, connected to the nozzle 6, are provided. A silicon substrate 3, having surface (100), is attached to the substrate retaining part 2, the disilane, acetylene and germanium are allowed to flow under control of a massflow controller, and a silicon epitaxial film is formed.



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